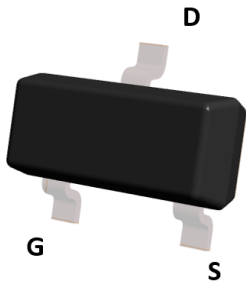
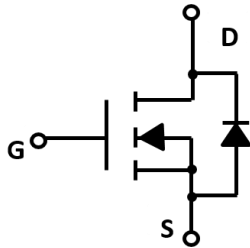
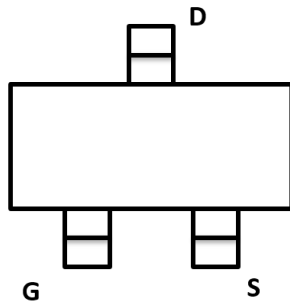


N-Channel Enhancement Mode Field Effect Transistor



Top View

SOT-23



Product Summary

- V_{DS} 60V
- I_D 340mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 2.5ohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 3.0ohm

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ C$ @ Steady State	340
		$T_A=70^\circ C$ @ Steady State	272
Pulsed Drain Current ^A	I_{DM}	1.5	A
Total Power Dissipation @ $T_A=25^\circ C$	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	357	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002	F2	7002.	3000	30000	120000	7" reel

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS1}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
	I_{GSS2}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 50	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=300mA$		1.2	2.5	Ω
		$V_{GS}=4.5V, I_D=200mA$		1.3	3.0	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=200mA$	80			ms
Diode Forward Voltage	V_{SD}	$I_S=300mA, V_{GS}=0V$			1.2	V
Maximum Body-Diode Continuous Current	I_S				340	mA
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1MHz$		27.5		pF
Output Capacitance	C_{oss}			2.75		
Reverse Transfer Capacitance	C_{rss}			1.9		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=0.3A$		1.6		nC
Gate-Source Charge	Q_{gs}			0.47		
Gate-Drain Charge	Q_{gd}			0.25		
Reverse Recovery Charge	Q_{rr}	$I_F=0.3A, di/dt=-100A/us$		2.5		ns
Reverse Recovery Time	t_{rr}			11.5		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=30V, I_D=300mA, R_{GEN}=6\Omega$		3.3		ns
Turn-on Rise Time	t_r			19		
Turn-off Delay Time	$t_{D(off)}$			9.6		
Turn-off fall Time	t_f			49		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

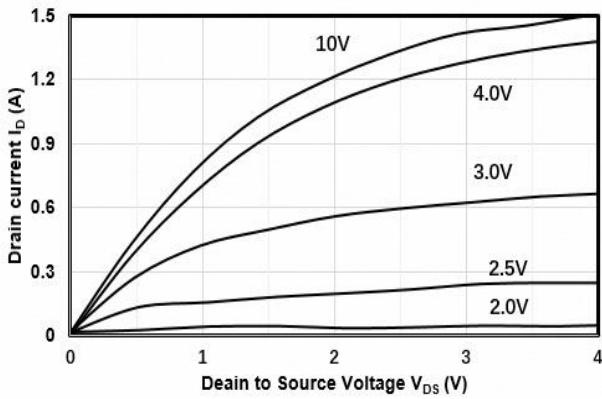


Figure1. Output Characteristics

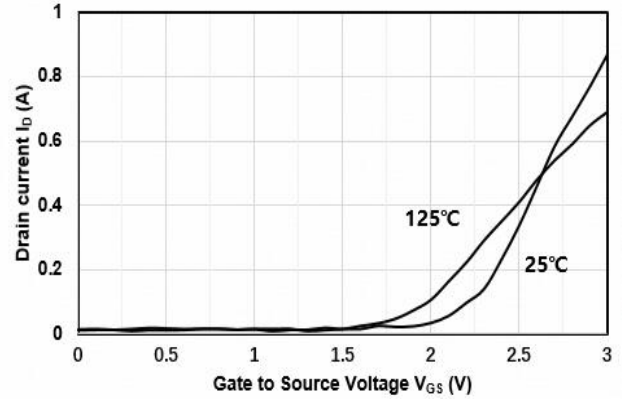


Figure2. Transfer Characteristics

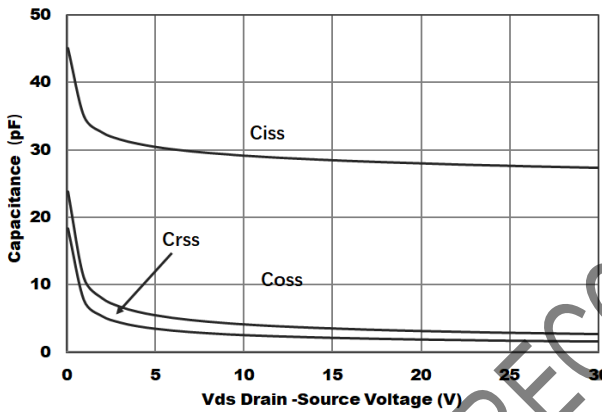


Figure3. Capacitance Characteristics

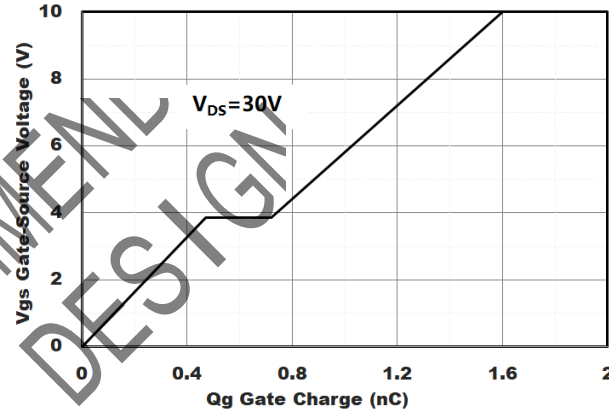


Figure4. Gate Charge

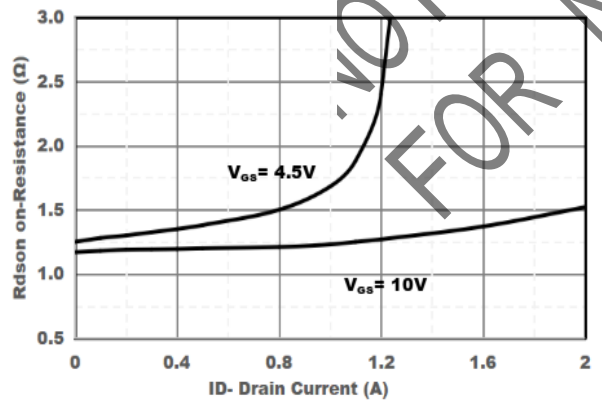


Figure5. Drain-Source on Resistance

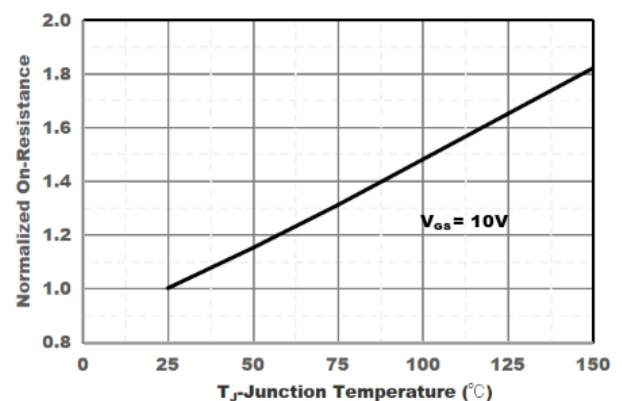


Figure6. Drain-Source on Resistance

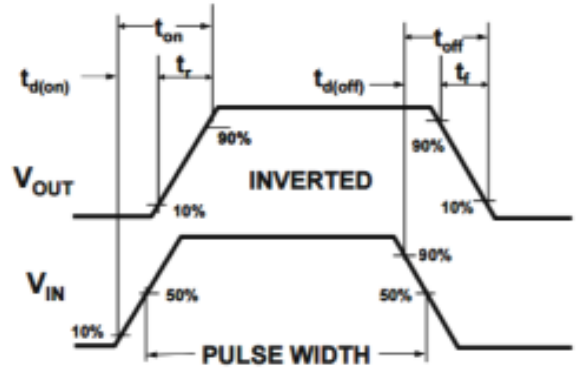
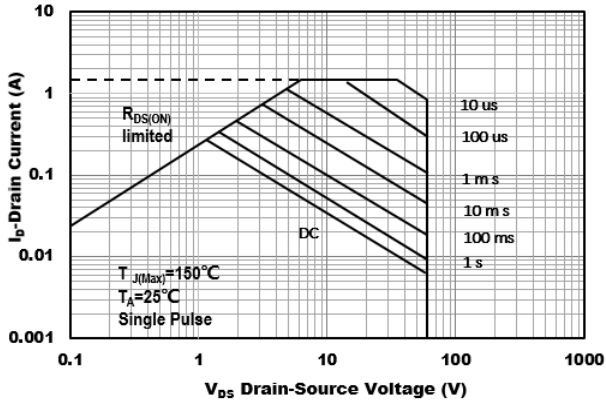


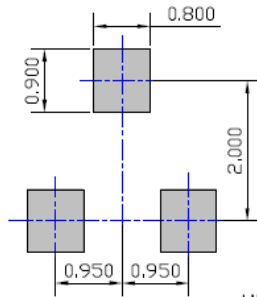
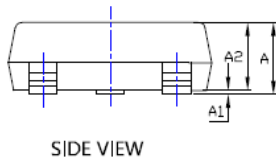
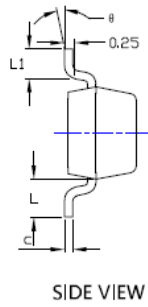
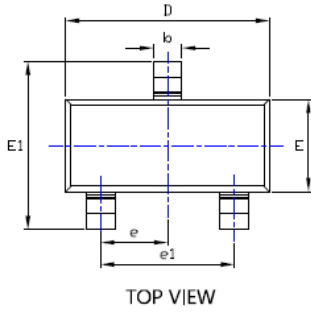
Figure7. Safe Operation Area

Figure8. Switching wave

NOT RECOMMEND
FOR NEW DESIGN



■ SOT-23 Package information



UNIT: mm

SYMBOL	INCHES			MILLimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.035	---	0.045	0.900	---	1.150
A1	0.000	---	0.004	0.000	---	0.100
A2	0.035	0.038	0.041	0.900	0.975	1.050
b	0.012	0.016	0.020	0.300	0.400	0.500
c	0.004	---	0.008	0.100	---	0.200
D	0.110	0.114	0.118	2.800	2.900	3.000
E	0.047	0.051	0.055	1.200	1.300	1.400
E1	0.089	0.094	0.100	2.250	2.400	2.550
e	0.037 TYP			0.950 TYP		
e1	0.071	0.075	0.079	1.800	1.900	2.000
L	0.022 REF			0.550 REF		
L1	0.012	0.016	0.200	0.300	0.400	0.500
φ	0*	---	8*	0*	---	8*

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS,
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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